

That is, the second conductive ring 326 may extend along the second row Row2. Although only a part of the second conductive ring 326 is illustrated, the second conductive ring 326 may be disposed to form a closed curve inside the semiconductor chip. The second conductive ring 326 may be connected to the second pad 322 through internal interconnection lines (not illustrated).

[0105] According to the example embodiments, instead of providing a separate input/output unit to include pads receiving a power supply voltage, a pad that receives a power supply voltage may be disposed in an input/output unit in which a pad that receives a ground voltage is disposed. For example, referring to FIG. 12, the second additional pad 322A is disposed in the fifth input/output unit (I/O Unit_5) separately provided to receive a ground voltage. That is, instead of providing a separate input/output unit to receive a power supply voltage, the second additional pad 322A may be disposed inside the fifth input/output unit (I/O Unit_5) in which a pad that receives a ground voltage is disposed. An SSN of a signal being input through the third pad 332 may be reduced by disposing the first pad 312 and the second additional pad 322A in one input/output unit. Also, a size of the semiconductor chip may be reduced.

[0106] FIG. 13 is a top plan view illustrating a part of a semiconductor chip in accordance with example embodiments. FIG. 14A is a cross-sectional view taken along the line A-A' of FIG. 13. FIG. 14B is a cross-sectional view taken along the line B-B' of FIG. 13. FIG. 14C is a cross-sectional view taken along the line C-C' of FIG. 13. FIG. 15A is a cross-sectional view taken along the line D-D' of FIG. 13. FIG. 15B is a cross-sectional view taken along the line E-E' of FIG. 13. FIG. 15C is a cross-sectional view taken along the line F-F' of FIG. 13.

[0107] Referring to FIGS. 13 through 15C, first pads 312 may be disposed along a first row Row1. A first conductive ring 316 may be disposed inside a semiconductor chip 300 under the first pads 312. The first pads 312 may be connected to the first conductive ring 316 through first internal interconnection lines 314. The first conductive ring 316 may be disposed inside the semiconductor chip 300 at a depth of h1. As illustrated in FIG. 14A, the first pads 312 may be connected to the first conductive ring 316 to have a minimum distance therebetween. That is, each of the first pads 312 may be connected to the first conductive ring 316 to have a length of h1 therebetween.

[0108] Second pads 322 may be disposed along a second row Row2. A second conductive ring 326 may be disposed inside the semiconductor chip 300 under the second pads 322. The second pads 322 may be connected to the second conductive ring 326 through second internal interconnection lines 324. The second conductive ring 326 may be disposed inside the semiconductor chip 300 to a depth of h2. As illustrated in FIG. 14B, the second pads 322 may be connected to the second conductive ring 326 to have a minimum distance therebetween. That is, each of the second pads 322 may be connected to the second conductive ring 326 to have a length of h2 therebetween.

[0109] In this case, some of the second pads (or second additional pads 322A) may be disposed along a third row Row3. A second additional internal interconnection line 324A may connect the second additional pad 322A to the second conductive ring 326. As illustrated in FIG. 15B, the second additional internal interconnection line 324A may be disposed in the form of an "L" character.

[0110] Third pads 332 may be disposed along the third row Row3. Third internal interconnection lines (not illustrated) may connect the third pads 332 to a logical circuit (not illustrated) and a signal input through the third pads 332 may be transmitted to the logical circuit through the third internal interconnection lines.

[0111] FIG. 16 is a drawing illustrating a part of FIG. 13 in three dimensions.

[0112] Referring to FIG. 16, the first pads 312 is disposed along the first row Row1 and the first conductive ring 316 is disposed inside the semiconductor chip 300 under the first pad 312. The first pad 312 is connected to the first conductive ring 316 to have a minimum distance therebetween through the first internal interconnection line 314.

[0113] Although not shown in FIG. 16, the second pads may be disposed along the second row and the second conductive ring may be disposed inside the semiconductor chip 300 under the second pad. The second pad and the second conductive ring may be connected to each other by the second internal interconnection line to have a minimum distance therebetween.

[0114] The second additional pad 322A is disposed on the third row Row3. The second additional pad 322A is connected to the second conductive ring 326 by a second additional internal interconnection line 324A having an "L" character shape. A shape of the second additional internal interconnection line 324A is not limited to the "L" character and the second additional internal interconnection line 324A may have various shapes.

[0115] Although not shown in FIG. 16, the third pads may be disposed along the third row Row3 and the third pads may be connected to a logical circuit (not illustrated) through the third internal interconnection lines.

[0116] The first pad 312 disposed on the first row Row1 is connected to the first conductive ring 316, and the second additional pad 322A disposed on the third row Row3 is connected to the second conductive ring 326. The first conductive ring 316 and the second conductive ring 326 may be connected to an ESD circuit (not illustrated) disposed inside the semiconductor chip 300. The ESD circuit may be connected to the logical circuit disposed inside the semiconductor chip 300 to stably supply a power supply voltage to the logical circuit. The third pads may be connected to the logical circuit disposed inside the semiconductor chip 300 by the third internal interconnection lines.

[0117] According to the example embodiments, instead of providing a separate input/output unit to supply a power supply voltage, the second additional pad 322A may be disposed in an input/output unit (e.g., I/O Unit_5) where the first pad 312 for supplying a ground voltage is disposed. That is, since a power supply voltage can be sufficiently supplied without providing a separate input/output unit for supplying a supply voltage, an SSN of a signal being input through the third pad 332 may be reduced. Additionally, since a separate input/output unit for supplying a ground voltage and a power supply voltage is omitted, a chip size may be reduced.

[0118] According to the example embodiments, a method of disposing pads of a semiconductor chip capable of stably supplying a power supply voltage may be provided.

[0119] According to the example embodiments, a method of disposing pads of a semiconductor chip capable of reducing a chip size may be provided.